

## NPN SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500/495

### Devices

2N5793

2N5794  
2N5794U

### Qualified Level

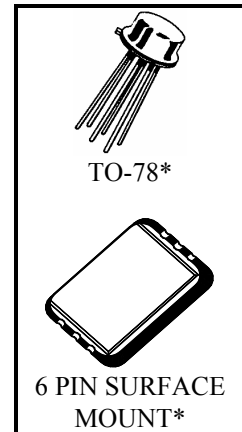
JAN  
JANTX  
JANTXV

### MAXIMUM RATINGS

Ratings	Symbol	Value		Units
Collector-Emitter Voltage	$V_{CEO}$	40		Vdc
Collector-Base Voltage	$V_{CBO}$	75		Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0		Vdc
Collector Current	$I_C$	600		mAdc
		<b>One Section<sup>(1)</sup></b>	<b>Total Device<sup>(2)</sup></b>	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	$P_T$	0.5	0.6	W
Operating & Storage Junction Temperature Range	$T_{op}, T_{stg}$	-65 to +200		$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$  for  $T_A > +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$  for  $T_A > +25^{\circ}\text{C}$



\*See MILPRF19500/495 for package outline

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Current $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	40		Vdc
Collector-Base Cutoff Current $V_{CB} = 75 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$	$I_{CBO}$		10 10	$\mu\text{Adc}$ $\eta\text{Adc}$
Emitter-Base Cutoff Current $V_{EB} = 6.0 \text{ Vdc}$ $V_{EB} = 4.0 \text{ Vdc}$	$I_{EBO}$		10 10	$\mu\text{Adc}$ $\eta\text{Adc}$

